

ORIGINALLY SUBMITTED INFORMAL DRAWINGS

YO994-065XX

Serial No. 08/999,663

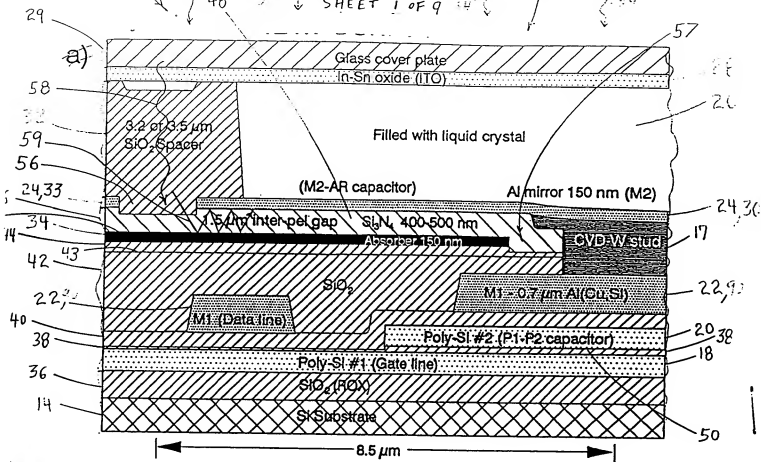


FIG 1

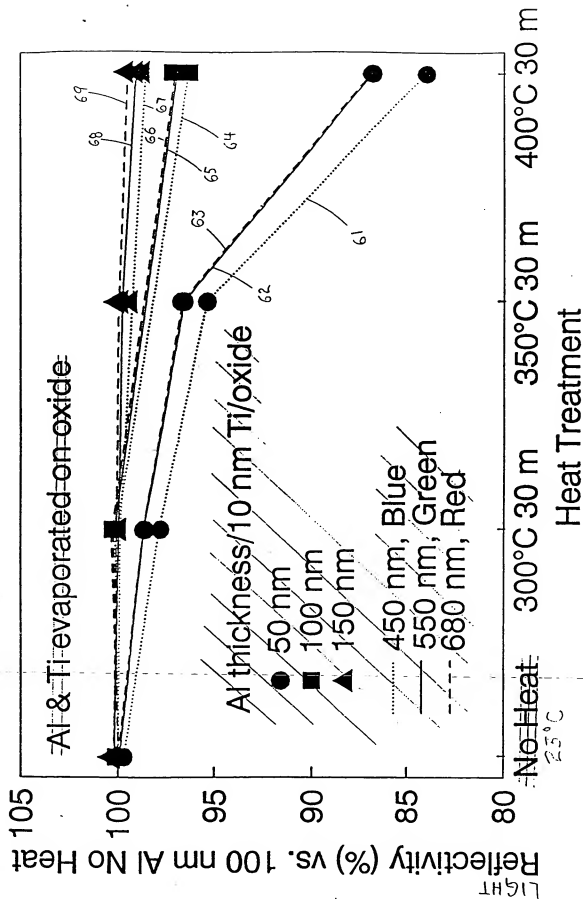


Fig. 2

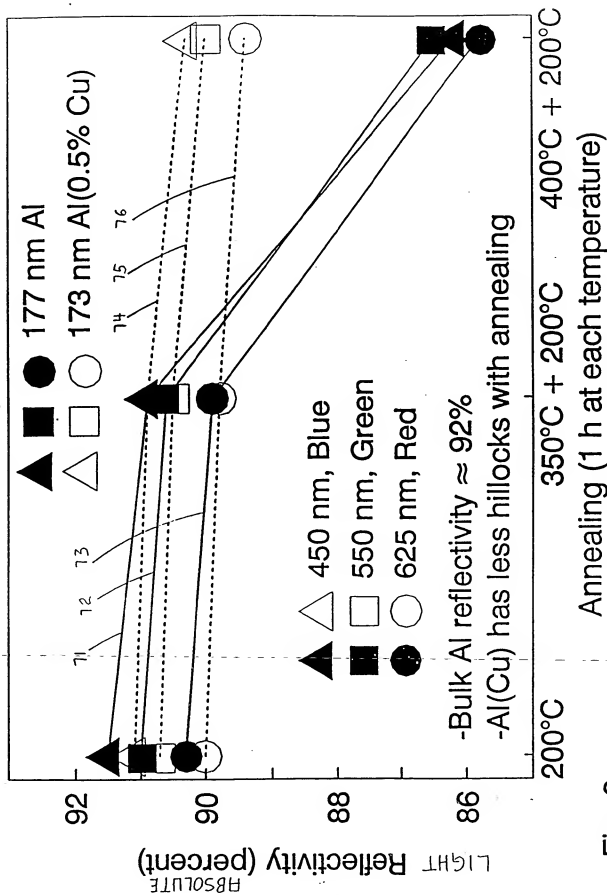
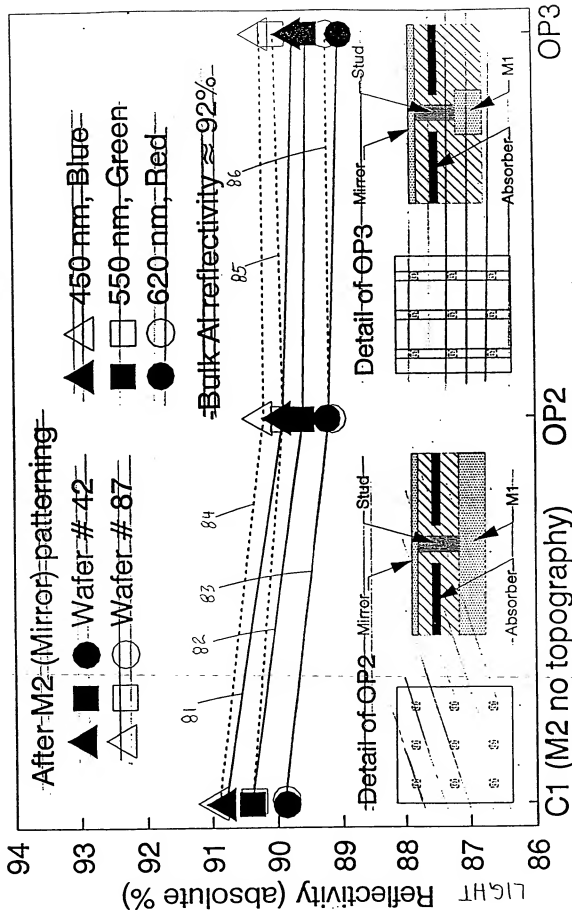


Fig. 3

ARCS



Test Structure

Fig. 4

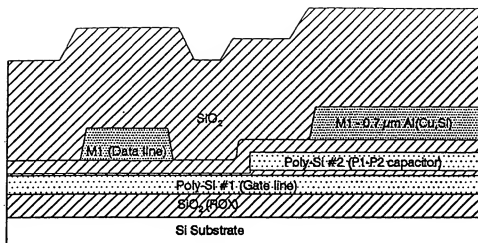


FIG 5

a) Liftoff 0.7 μm Al(Cu,Si) M1.
Deposit thick oxide.

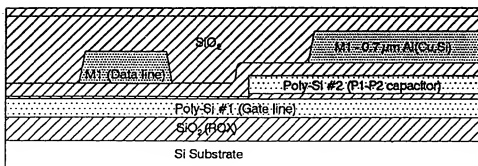


FIG 6

b) CMP oxide leaving 500 nm
on highest M1 point.
Deposit 200 nm oxide.

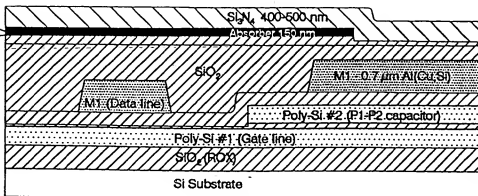


FIG 7

c) Deposit 10 nm Ti/ 100 nm
Al/ 50 nm TiN, pattern with
AR mask.
Deposit 400-500 nm nitride.

~~Fig. 5(a-c)~~

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ARC5A

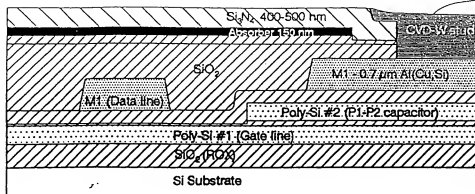
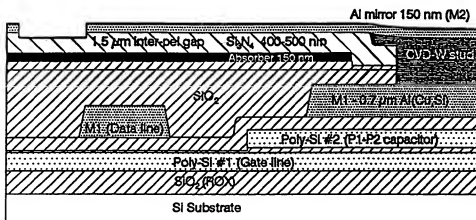
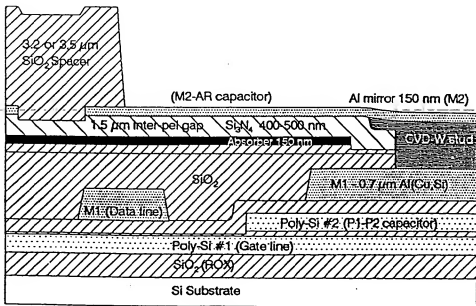


FIG 8

d) Pattern with V1 mask.
Deposit liner & CVD-W.
W Chem-mech polish.



e) Deposit 10 nm Ti/ 150 nm
Al, pattern with M2 mask.



f) Deposit 2.2 or 3 μm oxide,
pattern with SP mask. Open
up M1 pads with TV mask.

Fig. 5(d-f) FIG 10

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a) 15 μ m

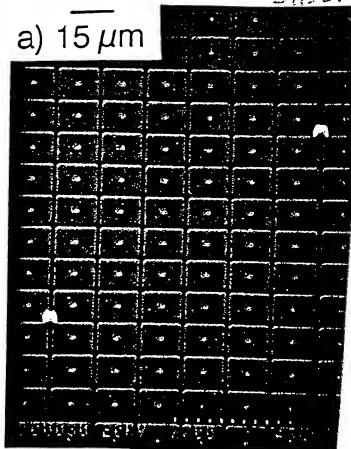


Fig. 11

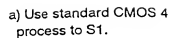
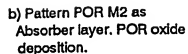
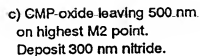


FIG. 12



∴ 13



~~Fig. 8(a-c)~~

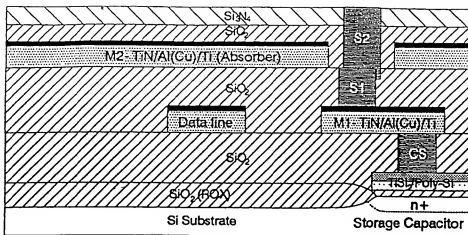


Fig 15

d) Pattern with S2 mask.
Deposit liner & CVD-W.
W Chem-mech polish.
Stacked S1&S2 to
connect M1 & M3.

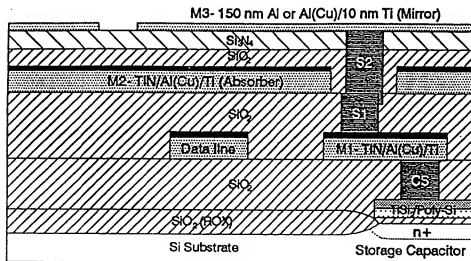
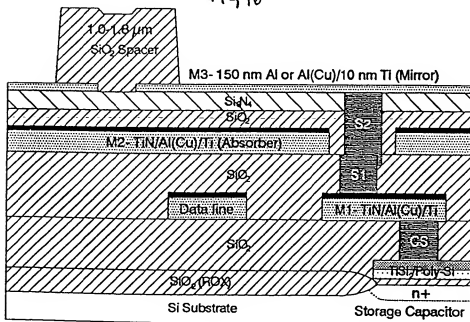


Fig 16

e) Deposit 10 nm Ti/ 150 nm
Al, pattern with M3 mask.



f) Deposit 1.0 or 1.8 μm oxide,
pattern with SP mask. Open
up M2 pads with TV mask.

Fig. 8(d-f)

Fig 17

ARC6B